

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1-5. (canceled)

6. (original) A method for manufacturing a semiconductor device, comprising:

forming an insulating film on a semiconductor substrate, said insulating film comprising at least a high-k insulating film that has higher dielectric constant than that of the silicon oxide film; and

selectively removing said insulating film via a wet etching with a chemical solution containing an organic solvent as a main component to partially expose said surface of said semiconductor substrate.

7-12. (canceled)

13. (original) The method according to claim 6, wherein said organic solvent is a solvent having polar group.

14-18. (canceled)

19. (original) The method according to claim 6, wherein said organic solvent is selected from the group consisting of: isopropyl alcohol; ethylene glycol; 2-heptanone; cyclopentanone; methylethyl ketone; glycol ether; propyleneglycol monomethyl ether; and propyleneglycol monomethyl acetate.

20-23. (canceled)

24. (original) The method according to claim 6, wherein said organic solvent is isopropyl alcohol, and said chemical solution contains not less than 90 % vol. of isopropyl alcohol.

25-30. (canceled)

31. (new) The method according to claim 6, further comprising, before said selectively removing said insulating film via a wet etching, forming a patterned protective film having a predetermined geometry on said insulating film; selectively removing a part of said high-k insulating film via a dry etching utilizing said protective film as a mask; and removing said protective film.

32. (new) The method according to claim 31, wherein in said selectively removing a part of said high-k insulating film via a dry etching, said dry etching is continued to a halfway to the entire thickness of said high-k insulating film.

33. (new) The method according to claim 6, further comprising, after said selectively removing said insulating film via a wet etching, rinsing the surface of said semiconductor substrate with an organic solvent, wherein in said selectively removing said insulating film via a wet etching, said chemical solution includes a fluoride-containing compound.